

IN THE CLAIMS

Please cancel claims 22, 27, 32 and 33 without prejudice.

Please amend the following claims.

1. (Currently Amended) A method of rinsing a wafer comprising:
spinning a wafer;
exposing said spinning wafer to DI water while providing sonic waves to substantially the entire surface area of the wafer; and
after exposing said spinning wafer to DI water, exposing said spinning wafer to a liquid or vapor having a lower surface tension than water.
2. (Currently Amended) The method of claim 1 wherein said liquid is or vapor comprises isopropyl alcohol (IPA).
3. (Currently Amended) The method of claim 1 ~~further comprising apply acoustic waves to said wafer while exposing said wafer to DI water~~ wherein said sonic waves are applied to the backside of said wafer.
4. (Original) The method of claim 1 further comprising the step of heating said DI water to a temperature greater than room temperature prior to exposing said spinning wafer to said DI water.
5. (Currently Amended) The method of claim 1 wherein said wafer is spun at a rate between 50-1000 rpms while exposing said wafer to said DI water and to said liquid or vapor.

6. (Currently Amended) The method of claim 2 wherein the time of exposure to said liquid is less than time of exposure to said DI water or vapor.

7. (Currently Amended) A method of rinsing a wafer comprising:
spinning said wafer;
exposing said spinning wafer to DI water; and
after exposing the frontside of said spinning wafer to said DI water, exposing said spinning wafer to ~~the vapor of a solution~~ a liquid or vapor having a lower surface tension than water while applying acoustic waves to said wafer.

8. (Currently Amended) The method of claim 7 wherein said ~~solution~~ liquid or vapor comprises is isopropyl alcohol (IPA).

9. (Original) The method of claim 7 further comprising apply acoustic waves to said wafer while exposing said wafer to DI water.

10. (Original) The method of claim 7 further comprising the step of heating said DI water to a temperature greater than room temperature prior to exposing said spinning wafer to said DI water.

11. (Currently Amended) The method of claim 7 wherein said wafer is spun at a rate between 50-1000 rpm while exposing said wafer to said DI water and to said liquid or vapor.

12. (Currently Amended) The method of claim 7 wherein the time of exposure to said liquid or vapor is less than time of exposure to said DI water.

13. (Currently Amended) A method of rinsing a wafer comprising:
spinning a wafer having a frontside and a backside;
exposing said frontside and backside of said spinning wafer to DI water; and
after exposing said spinning wafer to DI water, blowing a gas at the center of
the frontside of said wafer while said wafer is spinning.
14. (Original) The method of claim 13 wherein said gas is nitrogen (N₂).
15. (Original) The method of claim 13 further comprising applying acoustic waves
to said wafer while exposing said wafer to said DI water.
- 9/ 16. (Original) The method of claim 13 wherein said DI water is heated to a
temperature above room temperature prior to exposing said wafer to said DI water.
17. (Currently Amended) A method of rinsing a wafer comprising:
spinning a wafer having a frontside and a backside;
exposing said frontside of said spinning wafer to DI water; and
while exposing said spinning wafer to DI water, applying acoustic waves to
said backside of said spinning wafer.
18. (Original) The method of claim 17 wherein said acoustic waves have a
frequency in the range between 400 kHz and 8 MHz.
19. (Original) The method of claim 17 further comprising the step of after
exposing said wafer to said DI water exposing said spinning wafer to a liquid having a lower
surface tension than water.

20. (Original) The method of claim 17 wherein said DI water is heated to a temperature greater than room temperature.

21. (Currently Amended) A method of rinsing a wafer comprising:
spinning said wafer;
exposing said spinning wafer to DI water which has been heated to a temperature ~~greater than room temperature~~ between 60-70°C.

22. (Cancelled)

9/
23. (Original) The method of claim 21 further comprising applying acoustic waves to said wafer while exposing said wafer to said heated DI water.

24. (Original) The method of claim 21 further comprising after exposing said spinning wafer to said heated DI water, exposing said spinning wafer to a liquid having a lower surface tension than water.

25. (Currently Amended) A method of rinsing a wafer having a top surface and a bottom surface comprising:

spinning said wafer;
exposing said top surface of said spinning wafer to DI water heated to a temperature greater than room temperature;
while exposing said spinning wafer to said heated DI water, applying acoustic waves to said spinning wafer from a plate position beneath said bottom surface of said spinning wafer; and

after exposing said spinning wafer to said heated DI water, exposing said wafer to a liquid or vapor having lower surface tension than water.

26. (Currently Amended) A method of cleaning a wafer comprising:
spinning a wafer at a first rotation rate;
exposing said spinning wafer to an etchant or cleaning chemicals;
rinsing said cleaning chemicals or said etchant from said wafer with a rinsing method comprising:

spinning said wafer at a second rotation rate said second rotation rate faster than said first rotation rate;

dispensing DI water onto said spinning wafer; and
exposing said spinning wafer to a vapor or liquid having a lower surface tension than water; and

after rinsing said wafer, drying said wafer by spinning said wafer at a third rotation rate.

27. (Cancelled)

28. (Currently Amended) The method of claim ~~27~~26 wherein said second rotation rate is between 50-1000 rpm and said third rotation rate is between 500-2000 rpm.

29. (Currently Amended) The method of claim 26 wherein said liquid or vapor is comprises isopropyl alcohol.

30. (Original) The method of claim 26 wherein said rinsing method further comprises applying acoustic waves to said wafer while dispensing DI water on said wafer.

31. (Original) The method of claim 26 wherein said DI water is heated to a temperature greater than room temperature prior to dispensing said DI water on said spinning wafer.

32. (Cancelled)

91 33. (Cancelled)
